



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BVsss	Rss(on) Typ	Is Max TA = +25°C
12V	$5.3m\Omega$ @ V _{GS} = $3.8V$	16.6A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{SS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- · Battery Management
- Load Switch
- Battery Protection

Features

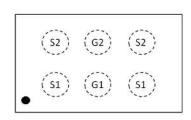
- CSP with Footprint 2.70mm x 1.81mm
- Height = 0.21mm for Low Profile
- ESD Protection of Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
 - For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

 https://www.diodes.com/quality/product-definitions/

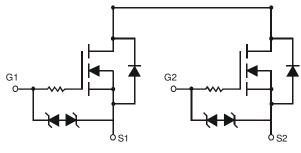
Mechanical Data

- Case: X3-DSN2718-6
- Terminal Connections: See Diagram Below
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0026 grams (Approximate)





X3-DSN2718-6



Top View Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN1006UCA6-7	X3-DSN2718-6	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\begin{array}{l} M2 = Product\ Type\ Marking\ Code \\ YM = Date\ Code\ Marking \\ Y\ or\ \overline{Y} = Year\ (ex:\ G = 2019) \\ M\ or\ \overline{M} = Month\ (ex:\ 9 = September) \end{array}$

Date Code Key

Year	2017	2018	20	019	2020	202	1	2022	2023	20:	24	2025
Code	E	F		G	Н			J	K	L		М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit			
Source-Source Voltage	Vsss	12	V			
Gate-Source Voltage	VGSS	±12	V			
Continuous Course Courset (Note 5) Vo. 4 5V	Steady	T _A = +25°C	I-	16.6	Α	
Continuous Source Current (Note 5) V _{GS} = 4.5V	State	T _A = +70°C	Is	13.2		
Continuous Course Current (Note 5) V 25V	Steady	T _A = +25°C	I-	12.1	A	
Continuous Source Current (Note 5) V _{GS} = 2.5V	State	T _A = +70°C	Is	9.7		
Pulsed Source Current (Note 6)	lsм	80	Α			

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7)	PD	1.0	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 7)	Reja	124.6	°C/W
Power Dissipation (Note 5)	PD	2.4	W
Thermal Resistance, Junction to Ambient @TA = +25°C (Note 5)	Reja	51.5	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

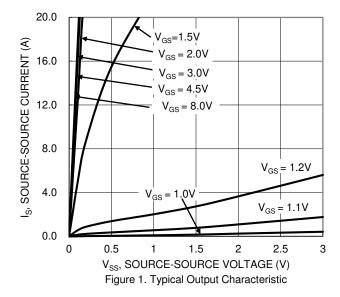
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

<u> </u>			_			
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Source-Source Breakdown Voltage	BV _{SSS}	12	_	_	V	$V_{GS} = 0V$, $I_S = 1mA$
Zero Gate Voltage Drain Current T _J = +25°C	I _{SSS}	_	_	1	μΑ	$V_{SS} = 10V V_{GS} = 0V$
Gate-Source Leakage	lgss	_	_	±10	μΑ	$V_{GS} = \pm 8V$, $V_{SS}=0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	_	1.3	V	Vss = 6V, $Is = 1mA$
		3.5	5.0	5.9		$V_{GS} = 4.5V, I_{S} = 3A$
		3.6	5.2	6.3		$V_{GS} = 4.0V, I_{S} = 3A$
Static Source-Source On-Resistance	Rss(on)	3.8	5.3	6.5	mΩ	$V_{GS} = 3.8V, I_{S} = 3A$
		3.8	5.5	8.0		Vgs = 3.1V, Is = 3A
		4.2	6.0	9.0		V _{GS} = 2.5V, I _S = 3A
Diode Forward Voltage	Vss	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 3A$
DYNAMIC CHARACTERISTICS (Note 9)	-					•
Input Capacitance	Ciss	_	2,360	_		N
Output Capacitance	Coss	_	666	_	pF	Vss = 6V, Vgs = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	325	1		1 = 1.01/11 12
Total Gate Charge	Qg	_	35.2	_		
Gate-Source Charge	Qgs	_	7.0	_	nC	$V_{SS} = 6V, V_{GS} = 4.5V,$
Gate-Drain Charge	Qgd	_	8.3	_	IIC	Is = 18A
Gate Charge at V _{TH}	Q _{g(TH)}	_	4.2	_		
Turn-On Delay Time	tD(ON)	_	615	_		
Turn-On Rise Time	t _R	_	1,447	_	no	$V_{SS} = 6V, V_{GS} = 4.5V,$
Turn-Off Delay Time	tD(OFF)	_	2,736	_	ns	Is = 3A
Turn-Off Fall Time	t⊧		3812	_		

Notes:

- 5. Device mounted on FR-4 material with 1inch² (6.45cm²), 2oz. (0.071mm thick) Cu.
- 6. Repetitive rating, pulse width limited by junction temperature.
- 7. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to production testing.





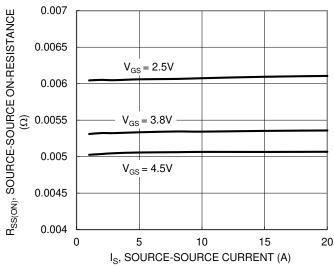


Figure 3. Typical On-Resistance vs. Source Current and Gate Voltage

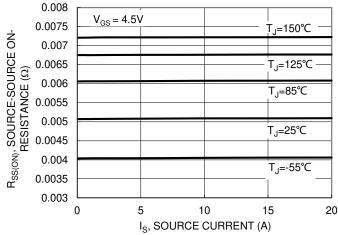


Figure 5. Typical On-Resistance vs. Source Current and Junction Temperature

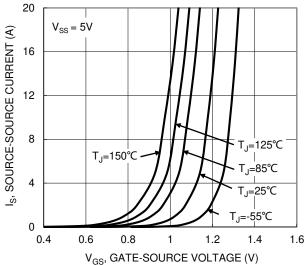


Figure 2. Typical Transfer Characteristic

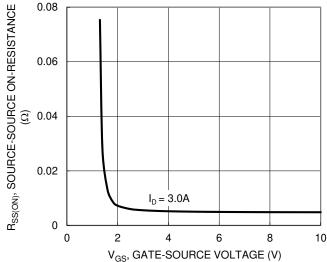


Figure 4. Typical Transfer Characteristic

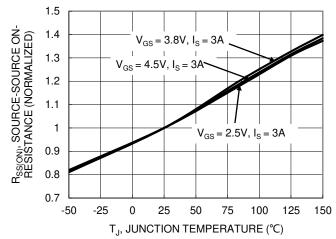


Figure 6. On-Resistance Variation with Junction Temperature



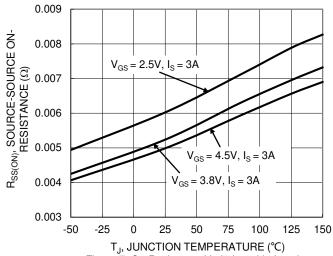


Figure 7. On-Resistance Variation with Junction
Temperature

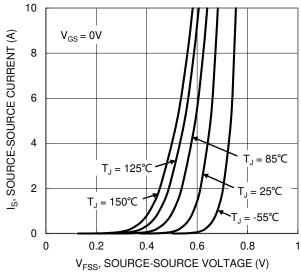
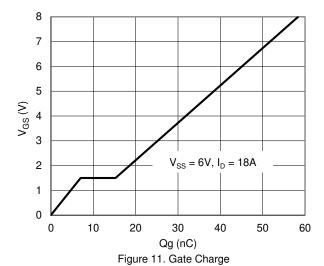


Figure 9. Diode Forward Voltage vs. Current



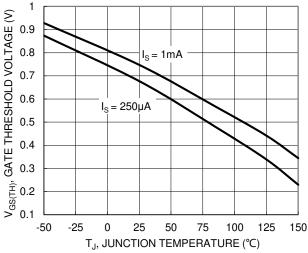
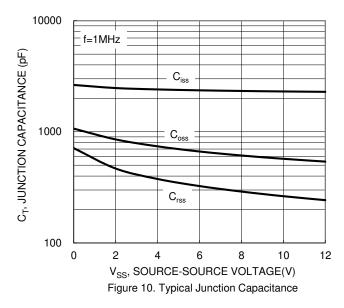
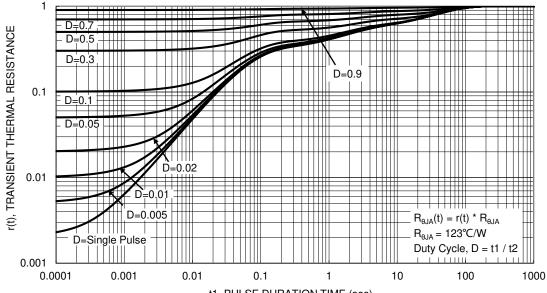


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 R_{DS(ON)} Limited IS, SOURCE-SOURCE CURRENT (A) =100µs 100 10 $P_{W} = 100 \text{ms}$ $T_{J(Max)} = 150 \,^{\circ}\text{C}$ $T_C = 25 \,^{\circ}\text{C}$ Single Pulse DUT on 1*MRP Board DC $V_{GS} = 10V$ 0.01 0.01 100 V_{SS}, SOURCE-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area





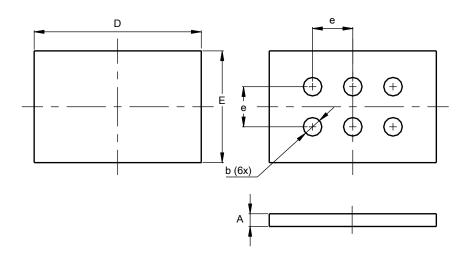
t1, PULSE DURATION TIME (sec) Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X3-DSN2718-6

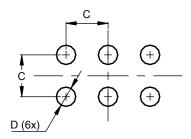


X3-DSN2718-6							
Dim	Dim Min Max Typ						
Α	0.16	0.26	0.21				
b	0.27	0.33	0.30				
D	2.65	2.75	2.70				
Е	1.76	1.86	1.81				
e 0.62 0.68 0.65							
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X3-DSN2718-6



Dimensions	Value (in mm)		
С	0.65		
D	0.30		



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